

Solution-possessed Vertical Photodetectors based on Composition Dependent Cesium Lead Halide (CsPbX_3 , X = Cl, Br, and I) Perovskite Quantum Dots (Erratum)

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A revised version of this manuscript was published on 27 February 2019. Details of the revision are provided in the text that accompanies this Erratum. The original paper has been updated.

The transmission electron microscope (TEM) of CsPbBr_3 QDs from (Adv. Optical Mater. 2017, 1700565) has been used as the TEM of CsPbBr_3 QDs in the inset of figure 2 in my paper (Proc. of SPIE Vol. 10914, 1091419, doi: 10.1117/12.2505580). However, the data has never been cited the above paper (Adv. Optical Mater. 2017, 1700565). We have added this citation as reference [23] in the revised manuscript.

Meanwhile, the photoresponse characteristics of the device has been incorrectly used as the photoresponse for parallel phototransistors in the inset of figure 3 (Adv. Optical Mater. 2017, 1700565). Correctly, the following figure presents the real photoresponse characteristics of the phototransistor.

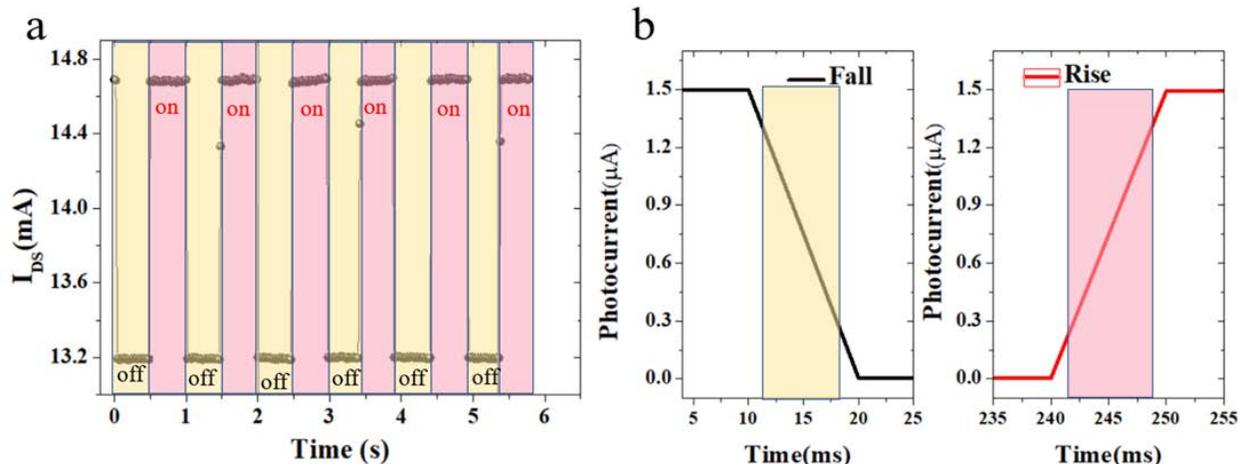


Figure 5. Photoresponse characteristics of perovskite phototransistor under irradiation with red light ($\lambda=632$ nm). (a) Current response of the device with a red light irradiance of 845 mW/cm^2 . (b) Temporal photocurrent responses highlighting a rise time of 6.5 ms and a decay time of 7.5 ms.